**Product data sheet** 

# 1. General description

Hyperfast power diode in a TO263 plastic package.





## 2. Features and benefits

- · Low leakage current
- Low thermal resistance
- · Low reverse recovery current
- · Reduces switching losses in associated MOSFET or IGBT

## 3. Applications

- Active PFC in air conditioner/EV charger/PV
- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes		<b>Values</b>		Unit
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage					V	
$I_{F(AV)}$	average forward current	$δ = 0.5$ ; square-wave pulse; $T_{mb} \le 130$ °C; Fig. 1; Fig. 2; Fig. 3		10			А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_{mb} \le$ 130 °C; square-wave pulse		20			А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4			135		А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse			148		Α
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.40	3.20	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.50	2.30	V
Dynamic	characteristics				,		
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 200 \text{ A/}\mu\text{s}$ ; $T_j = 25 \text{ °C}$ ; Fig. 7		-	13	-	ns

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	nc	no connected		v 14 A
2	K	cathode [1]		K <del>   </del> A 001aaa020
3	Α	anode	0	
mb	mb	mounting base; connected to cathod	1 3	

<sup>[1]</sup> It is not possible to connect to pin 2 of the TO-263 package.

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BYC10MB-650P	TO263	BYC10MB-650PJ	Reel	800	TO263d	17-Mar-2023

# 7. Marking

#### Table 4. Marking codes

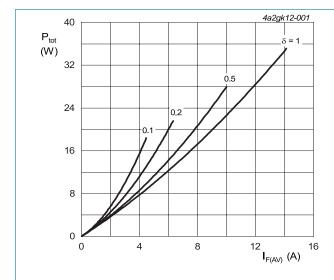
Type number	Marking codes
BYC10MB-650P	BYC10MB 650P

# 8. Limiting values

### **Table 5. Limiting values**

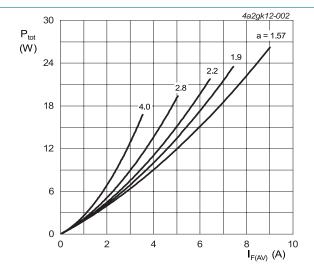
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage			650	V
$V_{\text{RWM}}$	crest working reverse voltage			650	V
V <sub>R</sub>	reverse voltage	DC		650	V
I <sub>F(AV)</sub>	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 130$ °C; Fig. 1; Fig. 2; Fig. 3		10	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 130 °C; square-wave pulse		20	А
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		135	А
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		148	Α
T <sub>stg</sub>	storage temperature			-65 to 175	°C
T <sub>j</sub>	junction temperature			-65 to 175	°C



$$\begin{split} I_{\text{F(AV)}} &= I_{\text{F(RMS)}} \times \sqrt{\delta} \\ V_{\text{o}} &= 1.728 \text{ V; } R_{\text{s}} = 0.0534 \text{ }\Omega \\ \end{split}$$
 Fig. 1. Forward power dissipation as a function of average forward current; square waveform;

maximum values



a = form factor =  $I_{F(RMS)}/I_{F(AV)}$  $V_o$  = 1.728 V;  $R_s$  = 0.0534  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

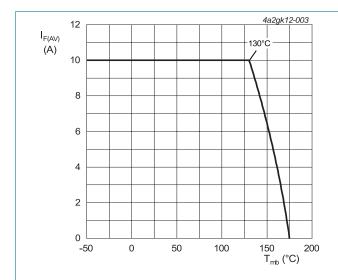


Fig. 3. Forward current as a function of mounting base temperature; maximum values

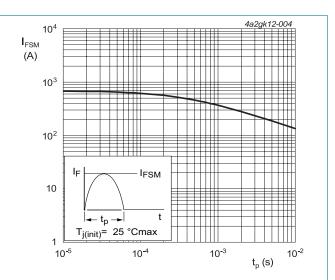


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	1.6	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air		-	60	-	K/W

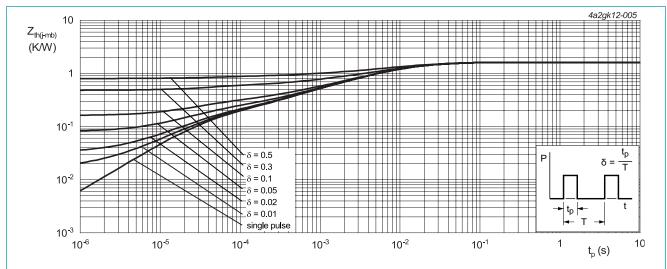
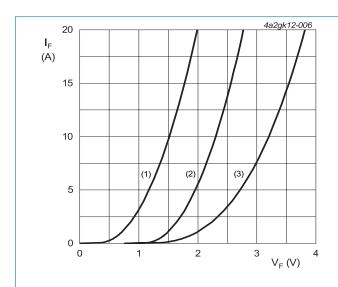


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

	indracteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	naracteristics						
$V_{F}$	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.40	3.20	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.50	2.30	V
$I_R$	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C		-	0.5	30	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C		-	0.1	0.8	mA
Dynamic	c characteristics						
Q <sub>r</sub>	reverse charge	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	37	-	nC
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	115	-	nC
T <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	13	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	29	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	48	-	ns
I <sub>RM</sub>	peak reverse recovery currentnon-repetitive	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	2.6	-	А
	avalanche energy	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	4.8	-	А
E <sub>as</sub>	non-repetitive avalanche energy	T <sub>j(init)</sub> = 25 °C		10.8	-	-	mJ



 $V_o$  = 1.728 V;  $R_s$  = 0.0534  $\Omega$ 

(1) T<sub>j</sub> = 150 °C; typical values (2) T<sub>j</sub> = 150 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values



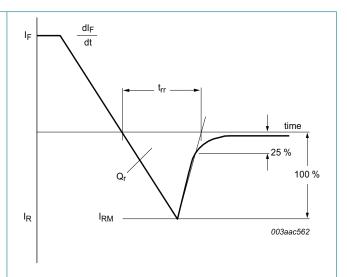


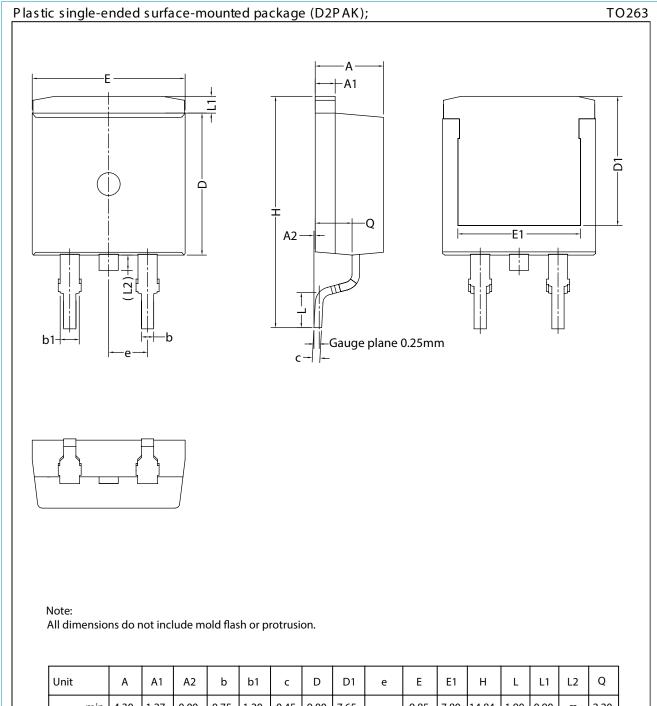
Fig. 7. Reverse recovery definitions; ramp recovery

BYC10MB-650P

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# 11. Package outline



l	Jnit		Α	A1	A2	b	b1	С	D	D1	e	E	E1	Н	L	L1	L2	Q
		min	4.30	1.27	0.00	0.75	1.20	0.45	9.00	7.65	2.54	9.85	7.80	14.84	1.90	0.90		2.20
Ľ	ММ	max	4.60	1.37	0.25	0.90	1.36	0.60	9.45	8.05	(BSC)	10.10	8.20	15.64	2.60	1.35	1.50	2.40

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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